

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)MAX}$	I_D
40V	$0.95m\Omega@10V$	353A

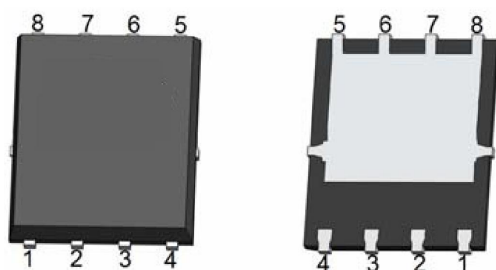
Feature

- Excellent gate charge x $R_{DS(on)}$ product(FOM)
- Very low on-resistance $R_{DS(on)}$
- Suffix "-Q1" for AEC-Q101

Application

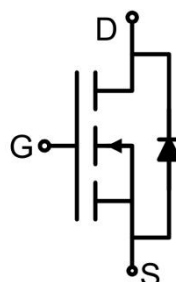
- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

Package

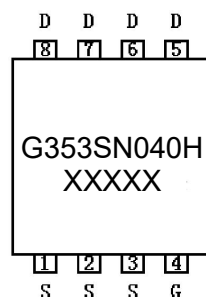


PDFN5*6-8L

Circuit diagram



Marking



Absolute maximum ratings ($T_c=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	40	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	I_D	353	A
Continuous Drain Current ($T_c = 100^{\circ}\text{C}$)	$I_D (100^{\circ}\text{C})$	223	A
Pulsed Drain Current	I_{DM}	1412	A
Single Pulse Avalanche Energy ¹⁾	E_{AS}	1797	mJ
Power Dissipation	P_D	200	W
Thermal Resistance Junction to Case	$R_{\theta JC}$	0.63	$^{\circ}\text{C}/\text{W}$
Operating Junction Temperature	T_J	$-55 \sim +150$	$^{\circ}\text{C}$
Storage Temperature Range	T_{STG}	$-55 \sim +150$	$^{\circ}\text{C}$

Electrical characteristics ($T_c=25^{\circ}\text{C}$, unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-source breakdown voltage	V _{(BR)DSS}	V _{GS} =0V, I _D =250μA	40			V
Zero gate voltage drain current	I _{DSS}	V _{DS} =40V, V _{GS} =0V			1	μA
Gate-body leakage current	I _{GSS}	V _{DS} =0V, V _{GS} =±20V			±100	nA
Gate threshold voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	2	3	4	V
Drain-source on-resistance	R _{DS(on)}	V _{GS} =10V, I _D =20A		0.72	0.95	mΩ
Dynamic characteristics ²⁾						
Input Capacitance	C _{iss}	V _{DS} =20V, V _{GS} =0V, f =1MHz		7150		pF
Output Capacitance	C _{oss}			2000		
Reverse Transfer Capacitance	C _{rss}			140		
Total Gate Charge	Q _g	V _{DS} =20V, V _{GS} =10V, I _D =20A		130		nC
Gate-Source Charge	Q _{gs}			27		
Gate-Drain Charge	Q _{gd}			30		
Turn-on delay time	t _{d(on)}	V _{DS} =20V, V _{GS} =10V, I _D =20A R _G =1.6Ω		25		nS
Turn-on rise time	t _r			48		
Turn-off delay time	t _{d(off)}			75		
Turn-off fall time	t _f			30		
Source-Drain Diode characteristics						
Diode Forward Current	I _S				353	A
Diode Forward voltage	V _{SD}	V _{GS} =0V, I _S =20A			1.2	V
Reverse Recovery Time	T _{rr}	I _F =20A, di/dt =100A/μs T _J = 25°C		98		nS
Reverse Recovery Charge	Q _{rr}			64		nC

Notes:

 1) EAS condition : $T_J = 25^{\circ}\text{C}, V_{DD} = 20\text{V}, V_G = 10\text{V}, L = 0.5\text{mH}, R_G = 25\Omega$.

2) Guaranteed by design, not subject to production testing.

Typical Characteristics

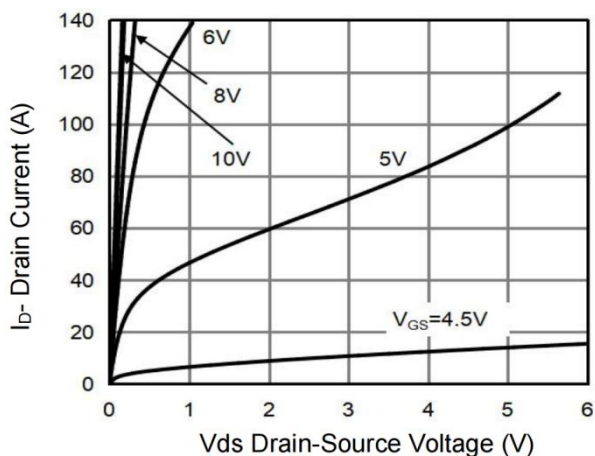


Figure 1 Output Characteristics

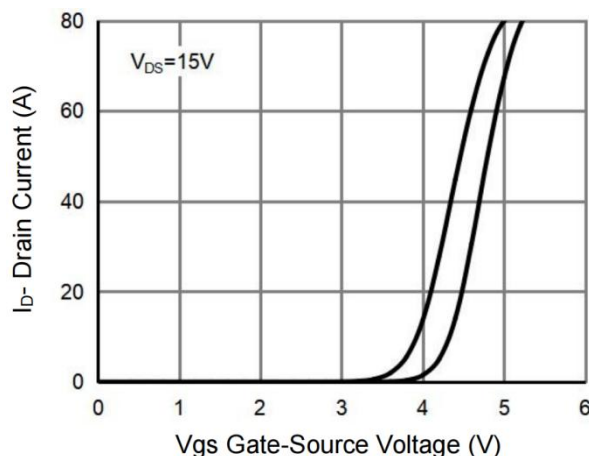


Figure 2 Transfer Characteristics

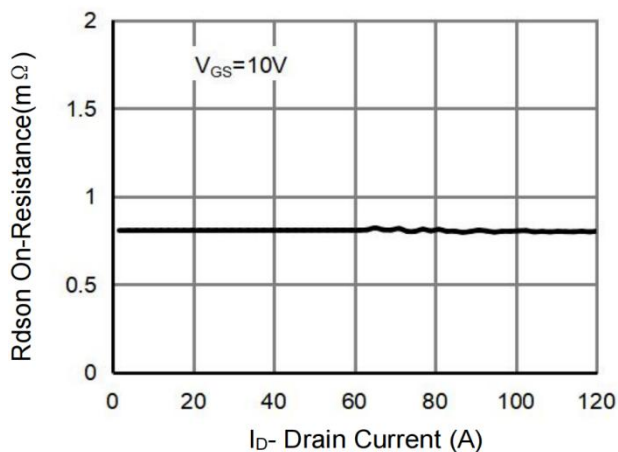


Figure 3 Rdson- Drain Current

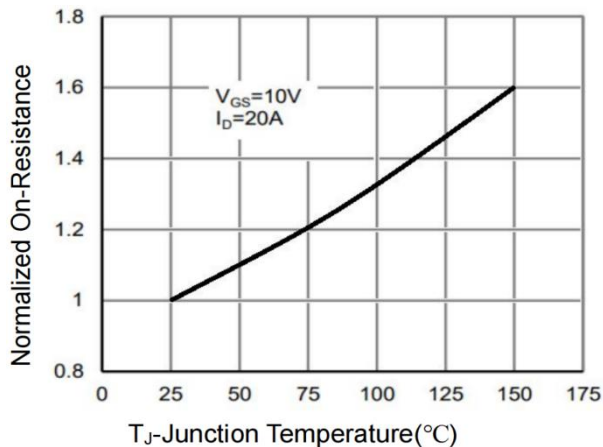


Figure 4 Rdson-Junction Temperature

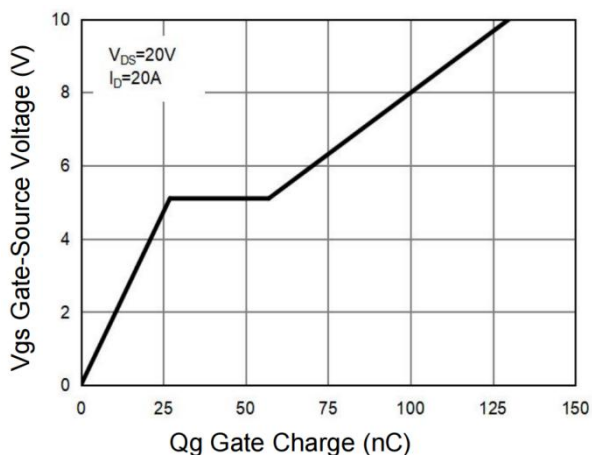


Figure 5 Gate Charge

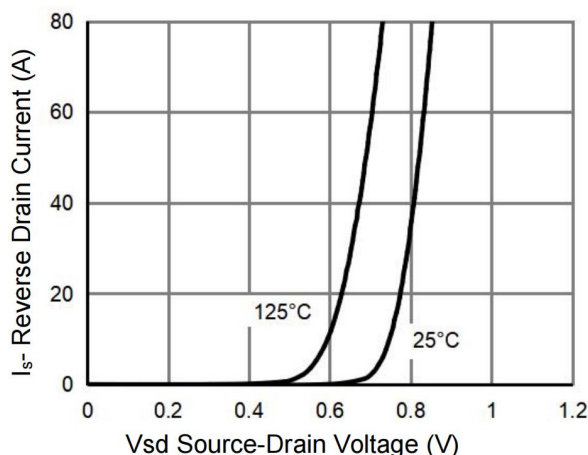


Figure 6 Source- Drain Diode Forward

Typical Characteristics

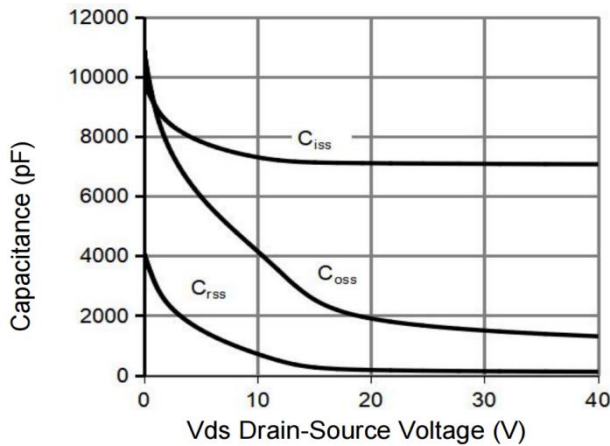


Figure 7 Capacitance vs Vds

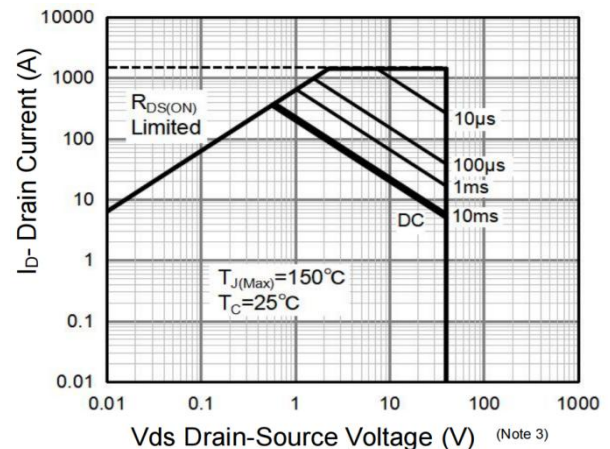


Figure 8 Safe Operation Area

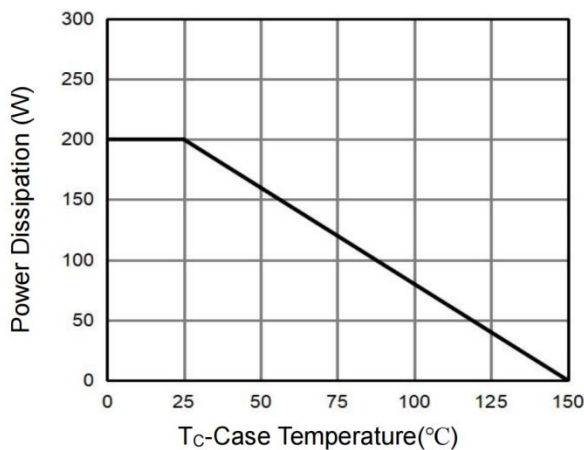


Figure 9 Power De-rating

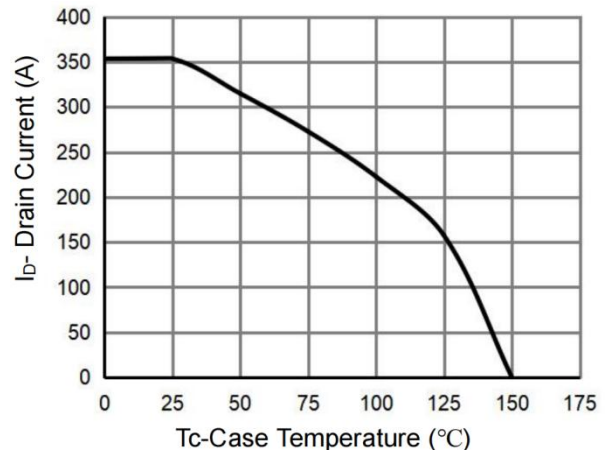


Figure 10 Current De-rating

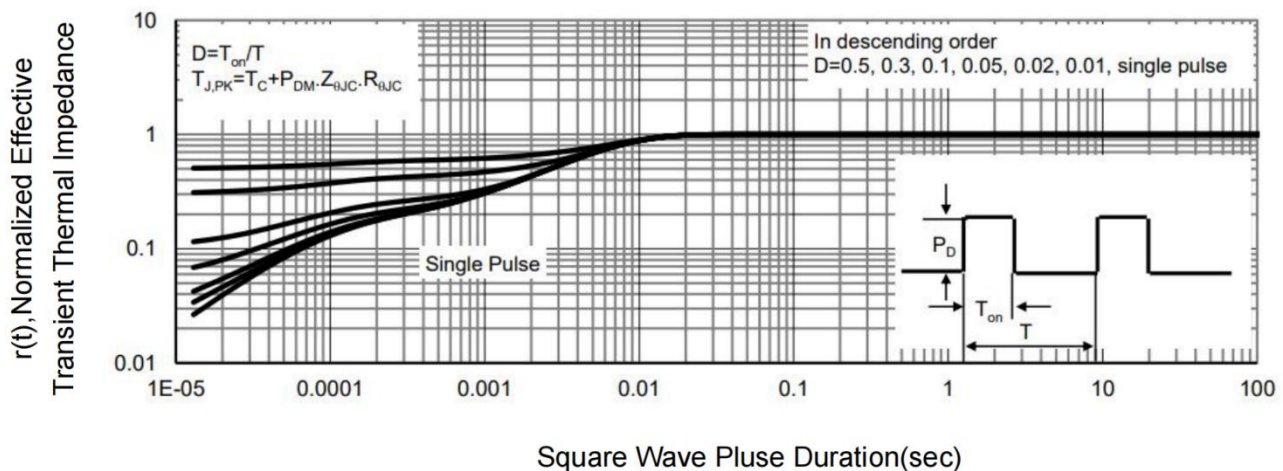
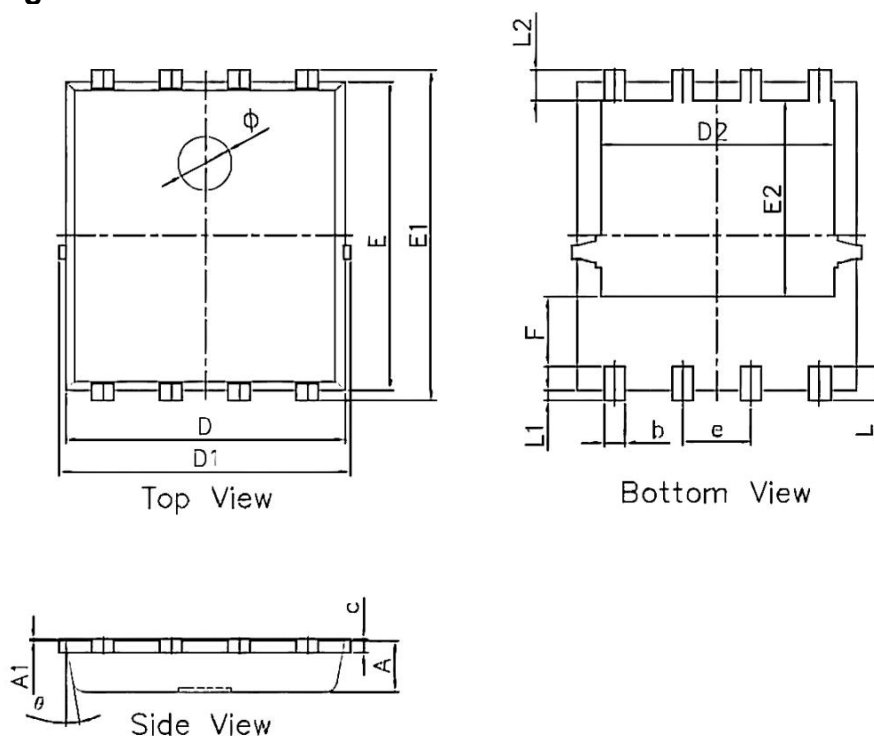


Figure 11 Normalized Maximum Transient Thermal Impedance

PDFN5*6-8L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.000	0.035	0.039
A1	0.000	0.005	0.000	0.000
b	0.350	0.500	0.014	0.020
c	0.200	0.300	0.008	0.012
D	5.100	5.300	0.201	0.209
D1	5.100	5.500	0.201	0.217
D2	4.250	4.450	0.167	0.175
e	1.270 BSC.		0.050 BSC.	
E	5.700	5.800	0.224	0.228
E1	6.000	6.300	0.236	0.248
E2	3.570	3.770	0.141	0.148
F	1.180	1.380	0.046	0.054
L	0.550	0.750	0.022	0.030
L1	0.150	0.250	0.006	0.010
L2	0.450	0.650	0.018	0.026
φ	0.900	1.100	0.035	0.043
θ	8°	12°	8°	12°